PRODUCT / PROCESS CHANGE NOTIFICATION

1. PCN basic data	
1.1 Company	STMicroelectronics International N.V
1.2 PCN No.	EMBEDDED PROCESSING/26/16581
1.3 Title of PCN	HHgrace Wuxi (China) Diffusion site additional source for STM32H74x and STM32H75x listed products.
1.4 Product Category	STM32H74x and STM32H75x
1.5 Issue date	2026-09-22

2. PCN Team	
2.1 Contact supplier	
2.1.1 Name	KRISZTINA NEMETH
2.1.2 Phone	+49 8946006
2.1.3 Email	krisztina.nemeth@st.com
2.2 Change responsibility	
2.2.1 Product Manager	Patrick AIDOUNE
2.1.2 Marketing Manager	Marie TOURNUT
2.1.3 Quality Manager	Pascal NARCHE

3. Change		
3.1 Category	3.2 Type of change	3.3 Manufacturing Location
Transfer	Line transfer for a full process or process brick (process step, control plan, recipes) from one site to another site: Wafer fabrication (SOP 2617)	HHGrace Wuxi (China)

4. Description of change		
	Old	New
4.1 Description	Front-end sources for STM32H74x and STM32H75x - ST Crolles (France) CR300 revision V	Front-end sources for STM32H74x and STM32H75x Existing : - ST Crolles (France) CR300 revision V Additional : - HHGrace Wuxi fab7 (China) revision 2 - HHGrace Wuxi fab9 (China) revision 3
4.2 Anticipated Impact on form,fit, function, quality, reliability or processability?	No change on Form, Fit or Function - same datasheet.	

5. Reason / motivation for change	
5.1 Motivation	Second source introduction
5.2 Customer Benefit	CAPACITY INCREASE

6. Marking of parts / traceability of change	
6.1 Description	Change is visible in the marking. Please refer to PCN 16581_Additional information.pdf document for further details.

7. Timing / schedule	
7.1 Date of qualification results	2026-09-08
7.2 Intended start of delivery	2026-10-15
7.3 Qualification sample available?	Upon Request

8. Qualification / Validation			
8.1 Description	16581 MDG-GPM-RER2304-PCN13841_14224_14728_15910_16068_16581 V6.0-ASE LQ7 LQ20 Cu RER Report.pdf		
8.2 Qualification report and qualification results	Available (see attachment)	Issue Date	2026-09-22

9. Attachments (additional documentations)
16581 Public product.pdf 16581 MDG-GPM-RER2304-PCN13841_14224_14728_15910_16068_16581 V6.0-ASE LQ7 LQ20 Cu RER Report.pdf 16581 _Additional information.pdf

10. Affected parts		
10. 1 Current		10.2 New (if applicable)
10.1.1 Customer Part No	10.1.2 Supplier Part No	10.1.2 Supplier Part No
	STM32H742IGK6	
	STM32H742IIK6	
	STM32H742IIT6	
	STM32H742VGT6	
	STM32H742VIT6	
	STM32H742VIT6TR	
	STM32H742ZIT6	
	STM32H743AGI6	
	STM32H743AII6	
	STM32H743IGT6	
	STM32H743IIK6	
	STM32H743IIK6TR	
	STM32H743IIT6	
	STM32H743VGT6	
	STM32H743VIH6	
	STM32H743VIH6TR	
	STM32H743VIT6	
	STM32H743VIT6TR	
	STM32H743XGH6	
	STM32H743XIH6	
	STM32H743XIH6TR	
	STM32H743ZGT6	
	STM32H743ZIT6	
	STM32H745IGK6	
	STM32H745IIK3	
	STM32H745IIK6	
	STM32H745IIT3	
	STM32H745IIT6	
	STM32H745XIH3	
	STM32H745XIH6	
	STM32H745ZGT6	
	STM32H745ZIT3	
	STM32H745ZIT6	
	STM32H747AII6	
	STM32H747IGT6	
	STM32H747IIT6	
	STM32H747XGH6	
	STM32H747XIH6	
	STM32H747ZIY6TR	
	STM32H750IBK6	
	STM32H750IBK6TR	
	STM32H750IBT6	
	STM32H750VBT6	
	STM32H750VBT6TR	

	STM32H750XBH6	
	STM32H750ZBT6	
	STM32H753AII6	
	STM32H753IIK6	
	STM32H753IIT6	
	STM32H753VIH6	
	STM32H753VIT6	
	STM32H753VIT6TR	
	STM32H753XIH6	
	STM32H753XIH6TR	
	STM32H753ZIT6	
	STM32H753ZIT6TR	
	STM32H755IIK3	
	STM32H755IIK6	
	STM32H755IIT3	
	STM32H755IIT6	
	STM32H755XIH3	
	STM32H755XIH6	
	STM32H755ZIT3	
	STM32H755ZIT6	
	STM32H757AII6	
	STM32H757IIT6	
	STM32H757XIH6	
	STM32H742BIT6	
	STM32H743BGT6	
	STM32H743BIT6	
	STM32H745BIT3	
	STM32H745BIT6	
	STM32H747BGT6	
	STM32H747BIT6	
	STM32H753BIT6	
	STM32H755BIT3	
	STM32H755BIT6	
	STM32H757BIT6	

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Public Products List

Publict Products are off the shelf products. They are not dedicated to specific customers, they are available through ST Sales team, or Distributors, and visible on ST.com

PCN Title : HHgrace Wuxi (China) Diffusion site additional source for STM32H74x and STM32H75x listed products.

PCN Reference : EMBEDDED PROCESSING/26/16581

Subject : Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

STM32H743XGH6	STM32H747XGH6	STM32H742XGH6
STM32H743VGT6	STM32H755ZIT6	STM32H750ZBT6
STM32H755XIH3TR	STM32H755XIH3	STM32H755XIH6
STM32H742VGH6	STM32H743VIT6	STM32H743VIT6TR
STM32H743IGK6	STM32H747XIH6	STM32H753XIH6
STM32H757XIH6	STM32H742AGI6	STM32H745XIH6
STM32H743IIT6	STM32H742VIH6	STM32H750VBT6
STM32H745XGH6	STM32H757XIH6A	STM32H750XBH6
STM32H750IBK6	STM32H742AII6	STM32H745IGK6
STM32H750IBT6	STM32H745ZIT6	STM32H745XIH3
STM32H753VIT6	STM32H745ZGT6	STM32H745XIH3TR
STM32H742XIH6	STM32H743XIH6	STM32H743ZGT6
STM32H743ZIT6	STM32H753ZIT6	STM32H742IGK6
STM32H755IIK3	STM32H743IGT6	STM32H753VIH6
STM32H742VIT6TR	STM32H757AII6	STM32H743AII6TR
STM32H755IIT3	STM32H745ZIT3	STM32H742VGT6TR
STM32H753AII6	STM32H747XIH6TR	STM32H753XIH6TR
STM32H753IIK6	STM32H742VIT6	STM32H745IIK3
STM32H742ZIT6	STM32H742IIK6	STM32H743VIH6
STM32H742AGI6TR	STM32H743VIH6TR	STM32H753IIT6
STM32H750VBT6TR	STM32H742ZGT6	STM32H742IIT6
STM32H747AGI6	STM32H747IGT6	STM32H757IIT6
STM32H743IIK6	STM32H742VGT6	STM32H742VIH6TR
STM32H745XIH6TR	STM32H747ZIY6TR	STM32H755IIT6
STM32H755XIH6TR	STM32H747AII6	STM32H745IGT6
STM32H743ZIT6TR	STM32H757ZIY6TR	STM32H747IIT6
STM32H755IIK6	STM32H743AII6	STM32H743VGH6
STM32H743AGI6	STM32H745IIK6	STM32H743IIK6TR
STM32H745IIT6	STM32H755ZIT3	STM32H745IIT3
STM32H747IIT3	STM32H753BIT6	STM32H743BIT6
STM32H742BGT6	STM32H743BGT6	STM32H745BIT3
STM32H745BGT6	STM32H755BIT6	STM32H747BGT6
STM32H747BIT6	STM32H757BIT6	STM32H742BIT6
STM32H745BIT6	STM32H755BIT3	

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Reliability Evaluation Report

MDG-GPM-RER2304

ASEKH LQFP7x7 to LQFP20x20 Copper Palladium wire

General Information	
Commercial Product	STM32L433VCT6, STM32H723ZGT6 STM32F427VIT6, STM32F217ZGT6 STM32L552VET6, STM32F767ZIT6 STM32G030C8T6, STM32U535RET6 STM32H533ZET6, STM32H742VGT6 STM32G474QET6
Product Line	435X66, 483X66, 419X66, 411X66 472X66, 451X66, 466X66, 455X66, 478X66, 450X66, 469X66
Die revision	435 cut1.1, 483 cut1.1, 419 cut2.2 411 cut2.4, 472 cut 2.1, 451 cut1.1 466 cut1.2, 455 cut1.1, 478 cut1.0, 450 cut2.2, 469 cut2.3
Product Description	STM32L4, STM32H7, STM32F4 STM32F2, STM32L5, STM32F7 STM32G0, STM32U5, STM32H5, STM32H7, STMG4
Package	LQFP 100 14x14x1.4 LQFP 144 20X20X1.4 LQFP 48 7x7x1.4 LQFP 64 10x10x1.4 LQFP 128 14x14x1.4
Silicon Technology	TN090, CMOSM40, CMOSM10, TN040, CMOSE40
Division	MDRF-GPAM

Traceability	
Diffusion Plant	TSMC Fab14 / Crolles 300/ HHGRACE
Assembly Plant	ASEKH - TAIWAN

Reliability Assessment	
Pass	X
Fail	

Release	Date	Author	Function
1.0	12/06/2023	Gabin BOSCO	GPAM BE Q&R
2.0	25/08/2023	Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R
3.0	05/07/2024	Celine NAVARRO	GPAM BE Q&R
4.0	28/10/2025	Celine NAVARRO	GPAM BE Q&R
4.1	21/01/2026	Celine NAVARRO	GPAM BE Q&R
4.2	04/03/2026	Celine NAVARRO	GPAM BE Q&R
5.0	16/04/2026	Celine NAVARRO	GPAM BE Q&R
6.0	09/09/2026	Gabin BOSCO	GPAM BE Q&R

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Approved by:

Approval list V1.0			
Name	**Function**	**Location**	**Date**
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	16/06/2023
Pascal NARCHE	Subgroup Quality Manager	ROUSSET	19/06/2023
Approval list V2.0			
Pascal NARCHE	Subgroup Quality Manager	ROUSSET	25/08/2023
Approval list V3.0			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	12/07/2024
Approval list V4.0			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	29/10/2025
Approval list V4.1			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	21/01/2026
Approval list V4.2			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	04/03/2026
Approval list V5.0			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	30/04/2026
Approval list V6			
Berengere ROUTIER-SCAPPUCCI	GPAM BE Q&R Manager	ROUSSET	11/09/2026

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RELIABILITY EVALUATION OVERVIEW

- **OBJECTIVE**

The aim of this report is to present the reliability evaluation performed for the qualification of ASEKH (Taiwan) LQFP7x7/LQFP10x10/LQFP14x14/LQFP20X20 with copper-palladium wires on M10 TSMC/Crolles, M40/E40 Crolles, M40 HHG and N90/N40 TSMC.

PCN13841 changes are described here below:

	Existing back-end line	Added back-end line
Assembly site	ASE KaoHsiung (Taiwan)	
Wire	Gold 0.8mil	CuPd 0.8mil
GLUE	Sumitomo CRM 1076WA	HITACHI EN4900G(1)
Marking composition	Without 2D	With 2D marking

PCN14224 changes are described here below:

	Existing back-end line	Added back-end line
Assembly site	AMKOR ATP (Philippines)	ASE KaoHsiung (Taiwan)
Wire	Gold 0.8mil	CuPd 0.8mil
GLUE	Evertech AP4200	HITACHI EN4900G(1)
Resin	SUMITOMO EME-G631SHQ	SUMITOMO EME-G631SH
Marking composition	Without 2D	With 2D marking

PCN 14728 changes are described here below:

	Existing back-end line		Added back-end line
Assembly site	ASE KaoHsiung (Taiwan)		
Wire	Gold 0.8mil		CuPd 0.8mil
GLUE	Sumitomo CRM 1076WA		HITACHI EN4900G
Marking composition	Without 2D	With 2D Marking	With 2D marking

(1)Sumitomo CRM 1076WA and HITACHI EN4900G glues were used during qualification phase however production will be on HITACHI EN4900G.

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PCN 15910 changes are described here below:

LQFP 10x10 64L	Existing back-end line			Added back-end line
Assembly site	StatsChipPAC JSCC Jiangyin (China)			ASE KaoHsiung (Taiwan)
Wire	Gold 0.8mil	Ag 96.5 0.8mil	CuPd 0.8 mil	CuPd 0.8 mil
Leadframe	Copper, Post plated			Copper, Post plated
Lead Finishing	Pure Tin (e3)			Pure Tin (e3)
Mold Compound	G631SHQ	G631SHQ	G700LALA	G631SH
Glue	Ablestik 3230	Ablestik 3230	EN4900GC	EN4900G
PP code marking	GQ			AA

PCN 16068 changes are described here below:

Table_1: Bill of material change description for LQFP 128L 14x14 package

LQFP 128L 14x14	Existing back-End assembly lines		New Added line
	Amkor ATP (Philippines)	**ASE Kaohsiung (Taiwan)**	
Molding Compound (2)	Sumitomo G631HQ	Sumitomo G631SH	
Die attach Glue	Evertech AP4200	SUMITOMO CRM 1076WA	HITACHI EN4900G
Bonding Wire	Gold 0.8 Mils		CuPd 0.8 Mils
Leadframe	Copper, post-plated		
Leadfinishing (1)	Pure Tin (e3)		
Marking composition	2D Marking		

(1) Lead color and surface finishing may slightly vary depending on lead finishing.
(2) Package darkness or chromaticity may change depending on molding compound.
Pin1 identifier may change in terms of size and positioning however remaining near pin1's edge.
Marking position and size may be different upon assembly site, without any loss of information.

PCN 16581 changes are described here below:

	Current condition	New condition	
Front-End Diffusion site	ST Crolles 300 (France)	HHGrace WuXi (China)	
		Fab 7	**Fab 9**
	STM32H75x, STM32H74x		
Die revision Marking **R**	**"V"**	**"2"**	**"3"**
Diffusion traceability plant code **WX**	"VQ"	"Y5"	"2E"

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- **CONCLUSION**

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Package oriented tests have not put in evidence any criticality. Physical analysis performed on samples submitted to tests has not put in evidence any issue. ESD CDM are in accordance with ST spec.

Based on the overall results obtained, products below have positively passed reliability evaluation:

Line code	Commercial product	Diff plant	Assy plant
435x66	STM32L433VCT6	TSMC FAB14	ASEKH (TAIWAN)
483x66	STM32H723ZGT6	Crolles 300	
419x66	STM32F427VIT6	TSMC FAB14	
411x66	STM32F217ZGT6	Crolles 300	
472x66	STM32L552VET6	TSMC FAB14	
451x66	STM32F767ZIT6	Crolles 300	
466x66	STM32G030C8T6	TSMC FAB14	
455x66	STM32U535RET6	TSMC FAB14	
478x66	STM32H533ZET6	Crolles 300	
450x66	STM32H742VGT6	HHGRACE	
469x66	STM32G474QET6	Crolles 300	

All reliability tests are completed with good results for all Finished Goods diffused in M10 TSMC/Crolles, M40/E40 Crolles, M40 HHGRACE, N90 TSMC/Crolles/Agrate, N40 TSMC and assembled in LQFP7x7 to LQFP20x20 at ASEKH (Taiwan) in copper-palladium wire.

Refer to Section 3.0 for reliability test results.

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1. RELIABILITY STRATEGY

Reliability trials performed as part of this reliability evaluation are in agreement with ST 0061692 specification, in full compliancy with the JESD-47 international standard.

PCN 15910 is covered by M10 Crolles technology qualified on ASE LQFP line with 2 reliability lots of 411 and 451 in LQ20x20 144L with same technology than STM32F446RCT6 (421 LQ64). Biggest packages size cover smaller package size qualification.

For details on test conditions, generic data used and specifications references, refer to test results summary in section 3.

2. PRODUCT OR TEST VEHICLE CHARACTERISTICS

2.1. Generalities

Package line	Partial rawline code	Number of lots
LQFP 100 14x14x1.4	1L*435	1
	1L*419	1
	1L*472	1
LQFP 144 20X20X1.4	1A*483	1
	1A*411	1
	1A*451	1
	1A*478	1
LQFP 48 7x7x1.4	5B*466	1
LQFP 64 10x10x1.4	5W*455	1
LQFP 100 14x14x1.4	1L*450	1
LQFP 128 14x14x1.4	TC*469	1

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2.2. Traceability

2.2.1. Wafer Fab Information

Die 435

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>TSMC Fab14 / Taiwan</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>TN090</td></tr>
<tr><td>Number of masks</td><td>45</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>PSG+NITRIDE / 1,75µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>10.045 mm² (3176.4µm, 3162.4µm)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>123,59 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/Ta/CuSeed/Cu</td><td>0.24 µm</td></tr>
<tr><td>2</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>3</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>4</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>5</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>6</td><td>TaN/Ta/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>7</td><td>AlCu</td><td>1.45 µm</td></tr>
</table>
</td></tr>
</table>

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Die 483

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>Crolles 300 / France</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>CMOSM40</td></tr>
<tr><td>Number of masks</td><td>51</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>PSG+NITRIDE / 1,75µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>15.67 mm² (3753µm, 4175µm)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>54.9,54.4 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/Ta/CuSeed/Cu</td><td>0.13 µm</td></tr>
<tr><td>2</td><td>TaN/Ta/CuSeed/Cu</td><td>0.14 µm</td></tr>
<tr><td>3</td><td>TaN/Ta/CuSeed/Cu</td><td>0.14 µm</td></tr>
<tr><td>4</td><td>TaN/Ta/CuSeed/Cu</td><td>0.14 µm</td></tr>
<tr><td>5</td><td>TaN/Ta/CuSeed/Cu</td><td>0.14 µm</td></tr>
<tr><td>6</td><td>TaN/Ta/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>7</td><td>TaN/Ta/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>8</td><td>Ta/TaN/AlCu</td><td>1.525 µm</td></tr>
</table>
</td></tr>
</table>

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Die 411

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>Crolles 300 / France</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>CMOSM10</td></tr>
<tr><td>Number of masks</td><td>42</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>PSG+NITRIDE / 1,75µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>14.71mm² (4006µm, 3674µm)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>59,123 µm</td></tr>
<tr><td>Rectangular</td><td>63,73 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/CuSeed/Cu</td><td>0.24 µm</td></tr>
<tr><td>2</td><td>TaN/CuSeed/Cu</td><td>0.33 µm</td></tr>
<tr><td>3</td><td>TaN/CuSeed/Cu</td><td>0.33 µm</td></tr>
<tr><td>4</td><td>TaN/CuSeed/Cu</td><td>0.33 µm</td></tr>
<tr><td>5</td><td>TaN/CuSeed/Cu</td><td>0.33 µm</td></tr>
<tr><td>6</td><td>TaN/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>7</td><td>AlCu/TinArc</td><td>1.45 µm</td></tr>
</table>
</td></tr>
</table>

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Die 419

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>TSMC Fab14 / Taiwan</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>CMOSM10</td></tr>
<tr><td>Number of masks</td><td>44</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>USG + NITRIDE / 1.1µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>25.43 mm² (5582µm, 4556µm)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>59,123 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/Ta/CuSeed/Cu</td><td>0.22 µm</td></tr>
<tr><td>2</td><td>TaN/Ta/CuSeed/Cu</td><td>0.28 µm</td></tr>
<tr><td>3</td><td>TaN/Ta/CuSeed/Cu</td><td>0.28 µm</td></tr>
<tr><td>4</td><td>TaN/Ta/CuSeed/Cu</td><td>0.28 µm</td></tr>
<tr><td>5</td><td>TaN/Ta/CuSeed/Cu</td><td>0.28 µm</td></tr>
<tr><td>6</td><td>Ta/TaN/AlCu</td><td>0.73 µm</td></tr>
<tr><td>7</td><td>AlCu</td><td>1.2 µm</td></tr>
</table>
</td></tr>
</table>

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Die 472

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>TSMC Fab14 / Taiwan</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>TN090</td></tr>
<tr><td>Number of masks</td><td>45</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>USG + NITRIDE / 1,75µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>17.999 mm² (4099.2, 4391.0)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>123,59 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/Ta/CuSeed/Cu</td><td>0.24 µm</td></tr>
<tr><td>2</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>3</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>4</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>5</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>6</td><td>TaN/Ta/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>7</td><td>AlCu</td><td>1.45 µm</td></tr>
</table>
</td></tr>
</table>

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Die 451

Wafer Fab Information	
FAB1	
Wafer fab name / location	Crolles 300 / France
Wafer diameter (inches)	12
Wafer thickness (µm)	775±25
Silicon process technology	CMOSM10
Number of masks	43
Die finishing front side (passivation) materials / thickness	PSG + NITRIDE / 1.1µm
Die finishing back side Materials	RAW SILICON
Die area (Stepping die size)	34.15 mm² (6130, 5572)

Die pad size

Geometry	Open(X,Y)
Rectangular	59,123 µm

Sawing street width (X,Y) (µm)	80,80

Metal levels/Materials/Thicknesses

Wire bond pad metal	Composition	Thickness
1	TaN/CuSeed/Cu	0.24 µm
2	TaN/CuSeed/Cu	0.33 µm
3	TaN/CuSeed/Cu	0.33 µm
4	TaN/CuSeed/Cu	0.33 µm
5	TaN/CuSeed/Cu	0.33 µm
6	TaN/CuSeed/Cu	0.85 µm
7	AlCu/TinArc	1.45 µm

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Die 466

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>TSMC Fab14 / Taiwan</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>TN090</td></tr>
<tr><td>Number of masks</td><td>45</td></tr>
<tr><td>Die finishing front side (passivation) materials / thickness</td><td>USG + NITRIDE / 1.1µm</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>4.0921 mm² (1889.6, 2165.6)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>65,59 µm</td></tr>
<tr><td>Rectangular</td><td>123,59 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>TaN/Ta/CuSeed/Cu</td><td>0.24 µm</td></tr>
<tr><td>2</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>3</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>4</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>5</td><td>TaN/Ta/CuSeed/Cu</td><td>0.31 µm</td></tr>
<tr><td>6</td><td>TaN/Ta/CuSeed/Cu</td><td>0.85 µm</td></tr>
<tr><td>7</td><td>AlCu</td><td>1.45 µm</td></tr>
</table>
</td></tr>
</table>

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Die 455

<table>
<tr><th colspan="2">Wafer Fab Information</th></tr>
<tr><th colspan="2">FAB1</th></tr>
<tr><td>Wafer fab name / location</td><td>TSMC Fab14 / Taiwan</td></tr>
<tr><td>Wafer diameter (inches)</td><td>12</td></tr>
<tr><td>Wafer thickness (µm)</td><td>775±25</td></tr>
<tr><td>Silicon process technology</td><td>N40</td></tr>
<tr><td>Number of masks</td><td>48</td></tr>
<tr><td>Die finishing front side (passivation) materials</td><td>Oxide + Nitride</td></tr>
<tr><td>Die finishing back side Materials</td><td>RAW SILICON</td></tr>
<tr><td>Die area (Stepping die size)</td><td>11.6035 mm² (3406.4, 3406.4)</td></tr>
<tr><td>Die pad size</td><td>
<table>
<tr><th>Geometry</th><th>Open(X,Y)</th></tr>
<tr><td>Rectangular</td><td>54.9,55.38 µm</td></tr>
<tr><td>Square</td><td>54.9,54.9 µm</td></tr>
</table>
</td></tr>
<tr><td>Sawing street width (X,Y) (µm)</td><td>80,80</td></tr>
<tr><td>Metal levels/Materials/Thicknesses</td><td>
<table>
<tr><th>Wire bond pad metal</th><th>Composition</th><th>Thickness</th></tr>
<tr><td>1</td><td>Cu</td><td>0.125 µm</td></tr>
<tr><td>2</td><td>Cu</td><td>0.145 µm</td></tr>
<tr><td>3</td><td>Cu</td><td>0.145 µm</td></tr>
<tr><td>4</td><td>Cu</td><td>0.145 µm</td></tr>
<tr><td>5</td><td>Cu</td><td>0.145 µm</td></tr>
<tr><td>6</td><td>Cu</td><td>0.850 µm</td></tr>
<tr><td>7</td><td>Cu</td><td>3.500 µm</td></tr>
<tr><td>8</td><td>Al</td><td>1.500 µm</td></tr>
</table>
</td></tr>
</table>

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Die 478

Wafer Fab Information	
FAB1	
Wafer fab name / location	Crolles 300 / France
Wafer diameter (inches)	12
Wafer thickness (µm)	775±25
Silicon process technology	CMOSE40
Number of masks	51
Die finishing front side (passivation) materials / thickness	PSG+NITRIDE / 1,75µm
Die finishing back side Materials	RAW SILICON
Die area (Stepping die size)	7.817 mm² (2785µm, 2807µm)
Die pad size	54.9,54.9 µm
Sawing street width (X,Y) (µm)	80,80
Metal levels/Materials/Thicknesses	

Wire bond pad metal	Composition	Thickness
1	TaN/Ta/CuSeed/Cu	0.145 µm
2	TaN/Ta/CuSeed/Cu	0.130 µm
3	TaN/Ta/CuSeed/Cu	0.130 µm
4	TaN/Ta/CuSeed/Cu	0.130 µm
5	TaN/Ta/CuSeed/Cu	0.130 µm
6	TaN/Ta/CuSeed/Cu	0.850 µm
7	TaN/Ta/CuSeed/Cu	0.850 µm
8	Ta/TaN/AlCu	1.525 µm

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Die 450

Wafer Fab Information	
FAB1	
Wafer fab name / location	HHGRACE Wuxi / HHGRACE WUXI DIFF
Wafer diameter (inches)	12
Wafer thickness (µm)	775±25
Silicon process technology	CMOSM40MI
Number of masks	51
Die finishing front side (passivation) materials / thickness	Oxide Nitride
Die finishing back side Materials	RAW SILICON
Die area (Stepping die size)	23.23 mm² (4983, 4662)
Die pad size	54.9,54.4 µm
Sawing street width (X,Y) (µm)	72,72
Metal levels/Materials/Thicknesses	

Wire bond pad metal	Composition	Thickness
1	TaN/Ta/Cu	0.13 µm
2	TaN/Ta/Cu	0.14 µm
3	TaN/Ta/Cu	0.14 µm
4	TaN/Ta/Cu	0.14 µm
5	TaN/Ta/Cu	0.14 µm
6	TaN/Ta/Cu	0.85 µm
7	TaN/Ta/Cu	0.85 µm
8	TaN/Ta/Ti/AlCu	1.525 µm

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Die 469

Wafer Fab Information	
FAB1	
Wafer fab name / location	Crolles 300 / France
Wafer diameter (inches)	12
Wafer thickness (µm)	775±25
Silicon process technology	TN090CE
Number of masks	43
Die finishing front side (passivation) materials / thickness	PSG+NITRIDE / 1,75µm
Die finishing back side Materials	RAW SILICON
Die area (Stepping die size)	17.390 mm² (4298.4, 4045.6)
Die pad size	123,59 µm
Sawing street width (X,Y) (µm)	80,80
Metal levels/Materials/Thicknesses	

Wire bond pad metal	Composition	Thickness
1	Ta/Tan/Cu	0.24 µm
2	TaN/Ta/Cu	0.33 µm
3	TaN/Ta/Cu	0.33 µm
4	TaN/Ta/Cu	0.33 µm
5	Ta/Tan/Cu	0.33 µm
6	TaN/Ta/Cu	0.9 µm
7	TaN/Ta/Ti/AlCu	1.45 µm

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2.2.2.Assembly Information

Assembly Information			
Package 1: LQFP 100 14x14x1.4	435	419	472 - 450
Assembly plant name / location	ASE Taiwan		
Pitch (mm)	0,5		
Die thickness after back-grinding (µm)	375±25		
Die sawing method	Laser groove + mechanical sawing		
Bill of Material elements			
Lead frame/ material/ reference	LF LQ14 100L Pure Tin C7025 6.6sq Slot		
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm		
Die attach material/ glue /supplier	GLUE SUMITOMO EPOXY CRM 1076WA		HITACHI EN4900G
Wire bonding material/diameter	Wire CuPd 0.8 mils		
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH		
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3		

Assembly Information				
Package 2: LQFP 144 20X20X1.4	483	411	451	478
Assembly plant name / location	ASE Taiwan			
Pitch (mm)	0.5			
Die thickness after back-grinding (µm)	375±25			
Die sawing method	Laser groove + mechanical sawing			
Bill of Material elements				
Lead frame/material/reference	LF LQ20 144L Pure Tin C7025 6.6sq			
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm			
Die attach material/glue/supplier	SUMITOMO EPOXY CRM 1076WA		HITACHI EN4900G	
Wire bonding material/diameter	Wire CuPd 0.8 mils			
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH			
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3			

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Assembly Information	
Package 3: LQFP 48 7x7x1.4	
Assembly plant name / location	ASE Taiwan
Pitch (mm)	0.5
Die thickness after back-grinding (µm)	375±25
Die sawing method	Laser groove + mechanical sawing
Bill of Material elements	
Lead frame/material/reference	LF LQ48L Pur tin C7025 4.092sq
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm
Die attach material/glue/supplier	HITACHI EN4900G
Wire bonding material/diameter	Wire CuPd 0.8 mils
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3

Assembly Information	
Package 4: LQFP 64 10x10x1.4	
Assembly plant name / location	ASE Taiwan
Pitch (mm)	0.5
Die thickness after back-grinding (µm)	375±25
Die sawing method	Laser groove + mechanical sawing
Bill of Material elements	
Lead frame/material/reference	LF LQ64 Pure Tin C7025 5.7sq
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm
Die attach material/glue/supplier	HITACHI EN4900G
Wire bonding material/diameter	Wire CuPd 0.8 mils
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3

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Assembly Information	
Package 5: LQFP 128 14x14x1.4	
Assembly plant name / location	ASE Taiwan
Pitch (mm)	0.4
Die thickness after back-grinding (µm)	375±25
Die sawing method	Laser groove + mechanical sawing
Bill of Material elements	
Lead frame/material/reference	LQ14 128L Pure Tin C7025 5.5sq
Lead frame finishing (material/thickness)	Pure Tin (e3): Tolerance 7 to 20µm
Die attach material/glue/supplier	HITACHI EN4900G
Wire bonding material/diameter	Wire CuPd 0.8 mils
Molding compound material/supplier/reference	MOLDING RESIN SUMITOMO EME-G631SH
Package Moisture Sensitivity Level (JEDEC J-STD020D)	3

2.2.3.Reliability testing information

Reliability Testing Information	
Reliability laboratory name / location	Grenoble Rel Lab, Rousset MDG Rel Lab, Shenzhen BE Lab, Muar BE Lab, ASE Rel Lab

Note: ST is ISO 9001 certified. This induces certification of all internal and subcontractor labs. ST certification document can be downloaded under the following link: http://www.st.com/content/st_com/en/support/quality-and-reliability/certifications.html

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3. TEST RESULTS SUMMARY

3.1. Lot information

Lot #	Diffusion Lot	Die Revision (Cut)	Trace Code	Raw Line	Package
Lot 1	9R113962	Cut1.1	AA136031	211L*435CSXZ	LQFP 100 14x14x1.4
Lot 2	3R31C302	Cut 1.1	AA143030	221A*483CSXZ	LQFP 144 20X20X1.4
Lot 3	VQ112465	Cut 2.4	AA136033	201A*411CSX2	LQFP 144 20X20X1.4
Lot 4	9R121544	Cut 2.2	AA136032	201L*419CSX5	LQFP 100 14x14x1.4
Lot 5	9R23159	Cut 2.1	AA248173	211L*472QCXZ	LQFP 100 14x14x1.4
Lot 6	Q229850	Cut 1.1	AA306008	201A*451QCXZ	LQFP 144 20X20X1.4
Lot 7	9R230180	Cut 1.2	AA249007	235B*466QCXY	LQFP 48 7x7x1.4
Lot 8	9R247270	Cut 1.1	AA351004	235W*455QCXZ	LQFP 64 10x10x1.4
Lot 9	VQ311272	Cut 1.0	AA345005	201A*478CSXA	LQFP 144 20X20X1.4
Lot 10	Y5452001	Cut 2.2	AA520072	241L*450QCX2	LQFP 100 14x14x1.4
Lot 11	VQ522388	Cut 2.3	AA603027	20TC*469QCX2	LQFP 128 14x14x1.4 1.0

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3.2. Test results summary

ACCELERATED ENVIRONMENT STRESS TESTS

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
PC	JSTD 020 JESD 22-A113 7191395	24h bake@125°C, MSL3 (192h/30°C/60%RH) 3x Reflow simulation Peak Reflow Temp= 260°C	10	308 Lot10: 231	3003	Lot 1: 0/308 Lot 5: 0/308 Lot 2: 0/308 Lot 6: 0/308 Lot 3: 0/308 Lot 7: 0/308 Lot 4: 0/308 Lot 8: 0/308 Lot 9: 0/308 Lot10: 0/231	NA
HTSL	JESD22-A103	Ta= 150°C Duration= 1000hrs ☑ After PC (excepted lot10)	10	77	770	Lot 1: 0/77 Lot 5: 0/77 Lot 2: 0/77 Lot 6: 0/77 Lot 3: 0/77 Lot 7: 0/77 Lot 4: 0/77 Lot 8: 0/77 Lot 9: 0/77 Lot10: 0/77	NA
TC	JESD22-A104	Ta= -65/150°C Cyc= 500 ☑After PC	10	77	770	Lot 1: 0/77 Lot 5: 0/77 Lot 2: 0/77 Lot 6: 0/77 Lot 3: 0/77 Lot 7: 0/77 Lot 4: 0/77 Lot 8: 0/77 Lot 9: 0/77 Lot10: 0/77	NA
THB	JESD22-A101	Ta=85°C/85%RH VDD=3v6 Duration= 1000hrs ☑After PC	10	77	770	Lot 1: 0/77 Lot 5: 0/77 Lot 2: 0/77 Lot 6: 0/77 Lot 3: 0/77 Lot 7: 0/77 Lot 4: 0/77 Lot 8: 0/77 Lot 9: 0/77 Lot10: 0/77	NA
UHAST	JESD22-A118	Ta=130°C ,85% RH, 2 Atm Duration= 96hrs ☑ After PC	10	77	770	Lot 1: 0/77 Lot 5: 0/77 Lot 2: 0/77 Lot 6: 0/77 Lot 3: 0/77 Lot 7: 0/77 Lot 4: 0/77 Lot 8: 0/77 Lot 9: 0/77 Lot10: 0/77	NA

ELECTRICAL TEST VERIFICATION

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
CDM	JEDEC JS-002	Voltage=500V for 411/466/ 455 (except PC15 250V)/ 478 Voltage=250V for 435/483/419/472/451/450/469	11	3	33	Lot 1: 0/3 Lot 5: 0/3 Lot 2: 0/3 Lot 6: 0/3 Lot 3: 0/3 Lot 7: 0/3 Lot 4: 0/3 Lot 8: 0/3 Lot 9: 0/3 Lot10: 0/3 Lot11: 0/3	NA

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PACKAGE ASSEMBLY INTEGRITY TESTS

Test code	Stress method	Stress Conditions	Lots Qty	S.S.	Total	Results/Lot Fail/S.S.	Comments:(N/A =Not Applicable)
CA	Construction analysis including -Wire bond shear -Wire bond pull	ST internal specifications	11	50	550	Lot 1: 0/50 Lot 2: 0/50 Lot 3: 0/50 Lot 4: 0/50 Lot 5: 0/50 Lot 6: 0/50 Lot 7: 0/50 Lot 8: 0/50 Lot 9: 0/50 Lot10: 0/50 Lot11: 0/50	SHZ-CA_21_00299 SHZ-CA_22_00003 SHZ-CA_21_00351 SHZ-CA_21_00298 SHZ-CA_23_00132 SHZ-CA_23_00275 SHZ-CA_23_00075 MDG Muar_24_00011 SHZ - CA_24_00066 SHZ - CA_25_00375 MDG Muar_26_00013

Note: Test method revision reference is the one active at the date of reliability trial execution.

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4. APPLICABLE AND REFERENCE DOCUMENTS

Reference	Short description
JESD47	Stress-Test-Driven Qualification of Integrated Circuits
SOP2.4.4	Record Management Procedure
SOP2.6.2	Internal Change Management
SOP2.6.7	Finished Good Maturity Management
SOP2.6.9	Package & Process Maturity Management in BE
SOP2.6.11	Program Management for Product Development
SOP2.6.17	Management of Manufacturing Transfers
SOP2.6.19	Front-End Technology Platform Development and Qualification
DMS 0061692	Reliability Tests and Criteria for Product Qualification
JEDEC JS-002	Electrostatic discharge (ESD) sensitivity testing charge device model (CDM)
JESD 22-A103	High Temperature Storage Life
J-STD-020	Moisture/reflow sensitivity classification for non-hermetic solid state surface mount devices
JESD22-A113	Preconditioning of non-hermetic surface mount devices prior to reliability testing
JESD22-A118	Unbiased Highly Accelerated temperature & humidity Stress Test
JESD22-A104	Temperature cycling
JESD22-A101	Temperature Humidity Bias

5. GLOSSARY

ESD-CDM	Electrostatic Discharge - Charged device model
CA	Construction analysis
HTSL	High Temperature Storage Life
PC	Preconditioning
TC	Temperature Cycling
THB	Temperature Humidity Bias
UHAST	Unbiased HAST (Highly Accelerated Stress Test)
DMS	ST Advanced Documentation Controlled system/ Documentation Management system

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6. REVISION HISTORY

Release	Date	Description
1.0	19/06/2023	Initial Release
2.0	16/06/2023	Added PCN14224
3.0	25/08/2023	Added PCN14728 with die 455 and 478
4.0	28/10/2025	Added PCN15910 (for die 421)
4.1	21/01/2026	Typo error page 15
4.2	04/03/2026	Typo error page 1
5.0	16/04/2026	Added PCN16068 with results die 469 + results die 450
6.0	09/09/2026	Added PCN16581

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PRODUCT/PROCESS CHANGE NOTIFICATION
PCN16581 – Additional Information

HHgrace Wuxi (China) Diffusion site additional source for STM32H74x and STM32H75x listed products.

MDRF – General Purpose and Automotive Microcontrollers Division (GPAM)

What are the changes?

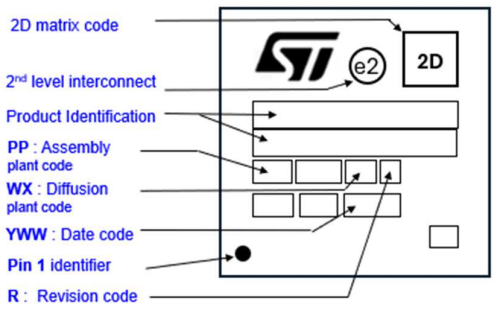
- STM32H75x/74x products will be transferred to HHGrace WuXi (China) FAB.
- The design database remains the same. No change in the silicon Die 450 cut2.2 version however in a second step a fix will be added to improve the yield at Electrical Wafer Sort.

How can the change be seen?

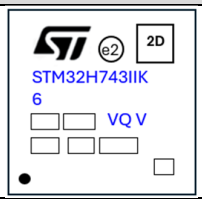
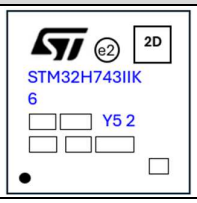
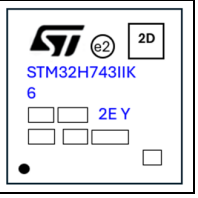
Table 1: Front-End Diffusion Sites

	Current condition	New condition	
Front-End Diffusion site	ST Crolles 300 (France)	HHGrace WuXi (China)	
		Fab 7	**Fab 9**
	STM32H75x, STM32H74x		
Die revision Marking **R**	**"V"**	**"2"**	**"3"**
Diffusion traceability plant code **WX**	"VQ"	"Y5"	"2E"

- **R - Die Revision changes** from (ST Crolles CR300) to (HHGrace Wuxi)
- **WX - Diffusion traceability plant code WX**
  - transferred from **VQ** (ST Crolles 300) to **Y5**/**2E** (HHGrace Wuxi) additional diffusion fab.



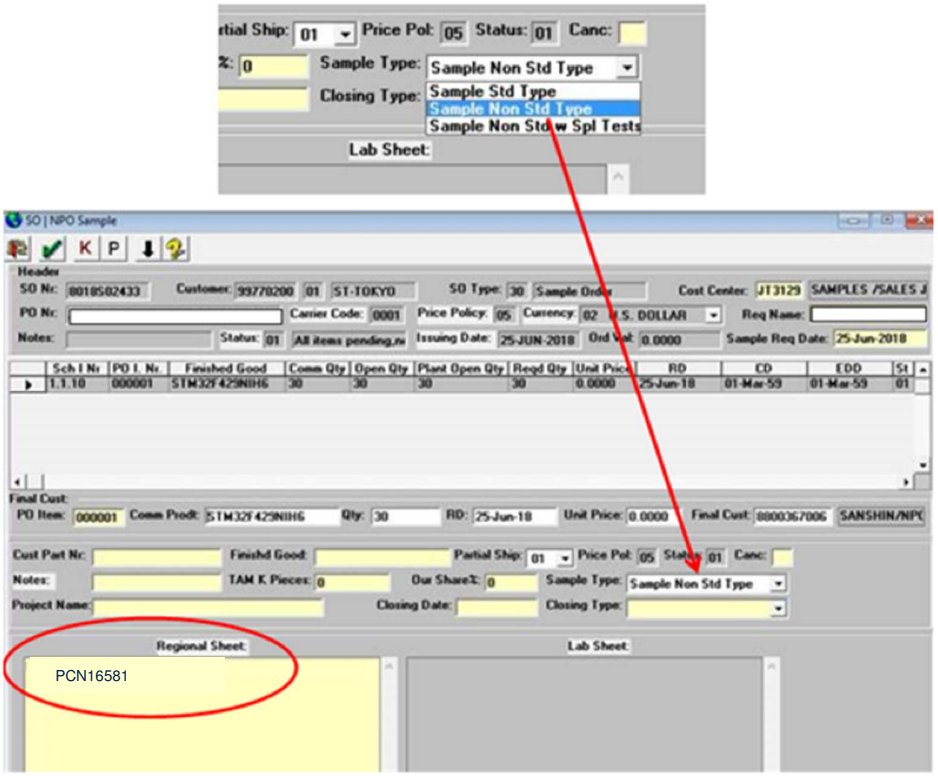
- **Marking Example** with Commercial product STM32H743IIK6 in **UFBGA 10X10** 176+25 package:

	Current condition	New condition	
Front-End Diffusion site	ST Crolles 300 (France)	HHGrace WuXi (China)	
		Fab 7	**Fab 9**
UFBGA 10X10 176+25 (ie STM32H743IIK6)			

How to order samples

For all samples request linked to this PCN, please:

- place a **Non-standard** sample order (choose Sample Non Std Type from pull down menu)
- insert the PCN number "**PCN16581**" into the NPO Electronic Sheet/**Regional Sheet**
- request sample(s) through Notice tool, indicating a single Commercial Product for each request



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